

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA2373FK

Low-Voltage Octal D-Type Latch with 3.6 V Tolerant Inputs and Outputs

The TC7MA2373FK is a high performance CMOS octal D-type latch. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

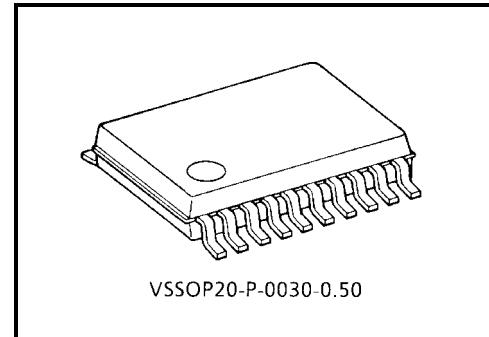
It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

This 8 bit D-type latch is controlled by a latch enable input (LE) and output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

The $26\ \Omega$ series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



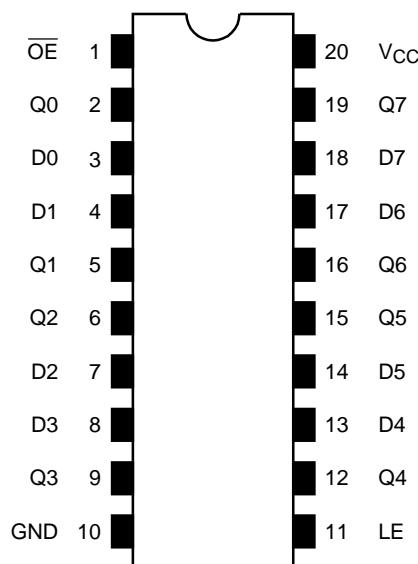
Weight: 0.03 g (typ.)

Features

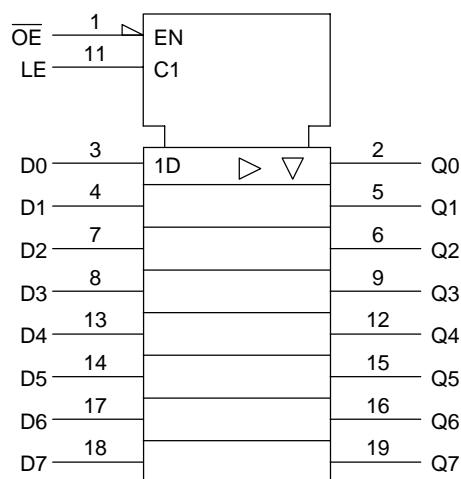
- 26 Ω series resistors on outputs.
- Low voltage operation: $V_{CC} = 1.8\text{--}3.6\text{ V}$
- High speed operation: $t_{pd} = 5.1\text{ ns (max)}\ (V_{CC} = 3.0\text{--}3.6\text{ V})$
 $t_{pd} = 6.1\text{ ns (max)}\ (V_{CC} = 2.3\text{--}2.7\text{ V})$
 $t_{pd} = 9.8\text{ ns (max)}\ (V_{CC} = 1.8\text{ V})$
- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 12\text{ mA (min)}\ (V_{CC} = 3.0\text{ V})$
 $I_{OH}/I_{OL} = \pm 8\text{ mA (min)}\ (V_{CC} = 2.3\text{ V})$
 $I_{OH}/I_{OL} = \pm 4\text{ mA (min)}\ (V_{CC} = 1.8\text{ V})$
- Latch-up performance: $\pm 300\text{ mA}$
- ESD performance: Machine model $> \pm 200\text{ V}$
Human body model $> \pm 2000\text{ V}$
- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)

*: To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Pin Assignment (top view)



IEC Logic Level



Truth Table

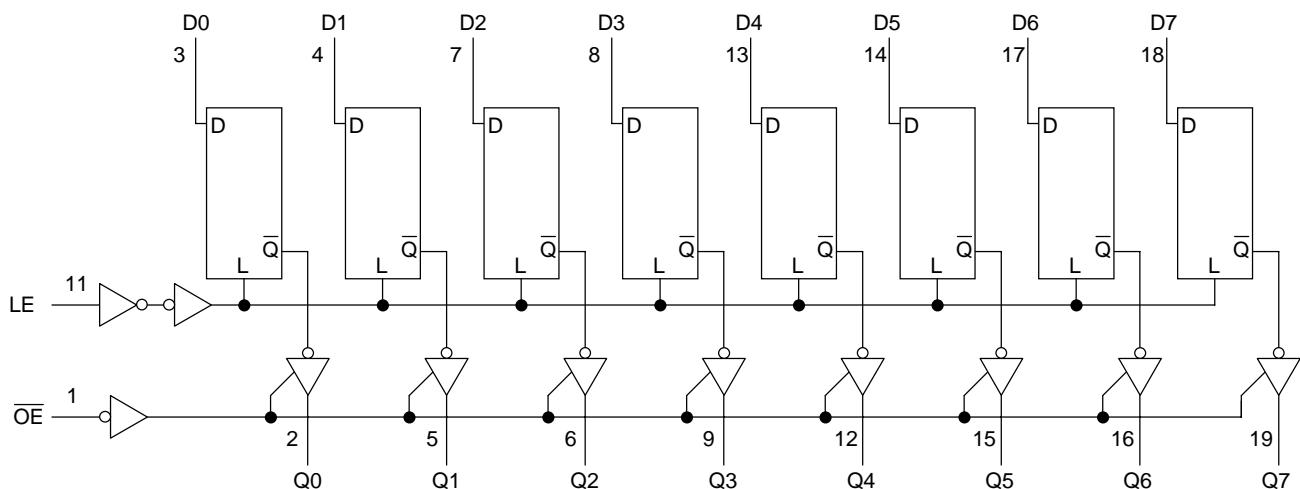
Inputs			Outputs
\overline{OE}	LE	D	
H	X	X	Z
L	L	X	Q_n
L	H	L	L
L	H	H	H

X: Don't care

Z: High impedance

Q_n : Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage	V _{IN}	-0.5~4.6	V
DC output voltage	V _{OUT}	-0.5~4.6 (Note1)	V
		-0.5~V _{CC} + 0.5 (Note2)	
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note3)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P _D	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note1: Off-state

Note2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note3: V_{OUT} < GND, V_{OUT} > V_{CC}

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	1.8~3.6	V
		1.2~3.6 (Note4)	
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	V _{OUT}	0~3.6 (Note5)	V
		0~V _{CC} (Note6)	
Output current	I _{OH} /I _{OL}	±12 (Note7)	mA
		±8 (Note8)	
		±4 (Note9)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V

Note4: Data retention only

Note5: Off-state

Note6: High or low state

Note7: V_{CC} = 3.0~3.6 V

Note8: V_{CC} = 2.3~2.7 V

Note9: V_{CC} = 1.8 V

Note10: V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V

Electrical Characteristics**DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} ≤ 3.6 V)**

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	High level		—	2.7~3.6					
	Low level	V _{IL}	—	2.7~3.6	—	0.8	—		
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	—	V	
				I _{OH} = -6 mA	2.7	2.2	—		
				I _{OH} = -8 mA	3.0	2.4	—		
				I _{OH} = -12 mA	3.0	2.2	—		
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7~3.6	—	0.2		
				I _{OL} = 6 mA	2.7	—	0.4		
				I _{OL} = 8 mA	3.0	—	0.55		
				I _{OL} = 12 mA	3.0	—	0.8		
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	—	±5.0	μA	
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		2.7~3.6	—	±10.0	μA	
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA	
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		2.7~3.6	—	20.0	μA		
		V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7~3.6	—	±20.0			
ΔI _{CC}		V _{IH} = V _{CC} - 0.6 V (per input)		2.7~3.6	—	750	μA		

DC Characteristics (Ta = -40~85°C, 2.3 V ≤ V_{CC} ≤ 2.7 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	High level		—	2.3~2.7					
	Low level	V _{IL}	—	2.3~2.7	—	0.7	—		
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	—	V	
				I _{OH} = -4 mA	2.3	2.0	—		
				I _{OH} = -6 mA	2.3	1.8	—		
				I _{OH} = -8 mA	2.3	1.7	—		
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3~2.7	—	0.2		
				I _{OL} = 6 mA	2.3	—	0.4		
				I _{OL} = 8 mA	2.3	—	0.6		
				I _{OL} = 12 mA	2.3~2.7	—	0.8		
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	—	±5.0	μA	
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		2.3~2.7	—	±10.0	μA	
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA	
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		2.3~2.7	—	20.0	μA		
		V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3~2.7	—	±20.0			

DC Characteristics ($T_a = -40\text{~}85^\circ\text{C}$, $1.8 \leq V_{CC} < 2.3$ V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	High level	V _{IH}	—		1.8~2.3	0.7 × V _{CC}	—	V	
	Low level	V _{IL}	—		1.8~2.3	—	0.2 × V _{CC}		
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	—	V	
				I _{OH} = -4 mA	1.8	1.4	—		
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	—	0.2		
				I _{OL} = 4 mA	1.8	—	0.3		
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		1.8	—	±5.0	μA	
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		1.8	—	±10.0	μA	
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		1.8	—	20.0	μA	
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		1.8	—	±20.0		

AC Characteristics (Ta = -40~85°C, Input: t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Propagation delay time (D-Q)	t _{pLH} t _{pHL}	Figure 1, Figure 2	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	6.1	
			3.3 ± 0.3	0.6	5.1	
Propagation delay time (LE-Q)	t _{pLH} t _{pHL}	Figure 1, Figure 2	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	6.3	
			3.3 ± 0.3	0.6	5.1	
3-state output enable time	t _{pZL} t _{pZH}	Figure 1, Figure 3	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	6.5	
			3.3 ± 0.3	0.6	5.0	
3-state output disable time	t _{pLZ} t _{pHZ}	Figure 1, Figure 3	1.8	1.5	7.7	ns
			2.5 ± 0.2	0.8	4.3	
			3.3 ± 0.3	0.6	3.9	
Minimum pulse width (LE)	t _w (H)	Figure 1, Figure 2	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum set-up time	t _s	Figure 1, Figure 2	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum hold time	t _h	Figure 1, Figure 2	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Output to output skew	t _{osLH} t _{osHL}	(Note11)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.

$$(tosLH = |t_{pLHm} - t_{pLHn}|, tosHL = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics (Ta = 25°C, Input: t_r = t_f = 2.0 ns, C_L = 30 pF)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{O LP}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note12)	1.8	0.15	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note12)	2.5	0.25	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note12)	3.3	0.35	
Quiet output minimum dynamic V _{OL}	V _{O LV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note12)	1.8	-0.15	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note12)	2.5	-0.25	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note12)	3.3	-0.35	
Quiet output minimum dynamic V _{OH}	V _{O HV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note12)	1.8	1.55	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note12)	2.5	2.05	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note12)	3.3	2.65	

Note12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

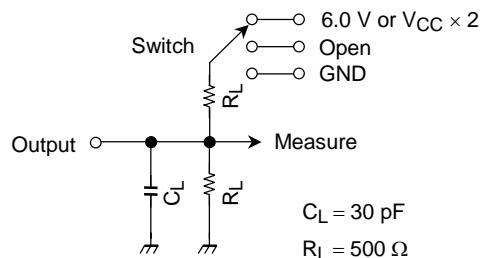
Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Output capacitance	C _O	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note13)	1.8, 2.5, 3.3	20	pF

Note13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$$

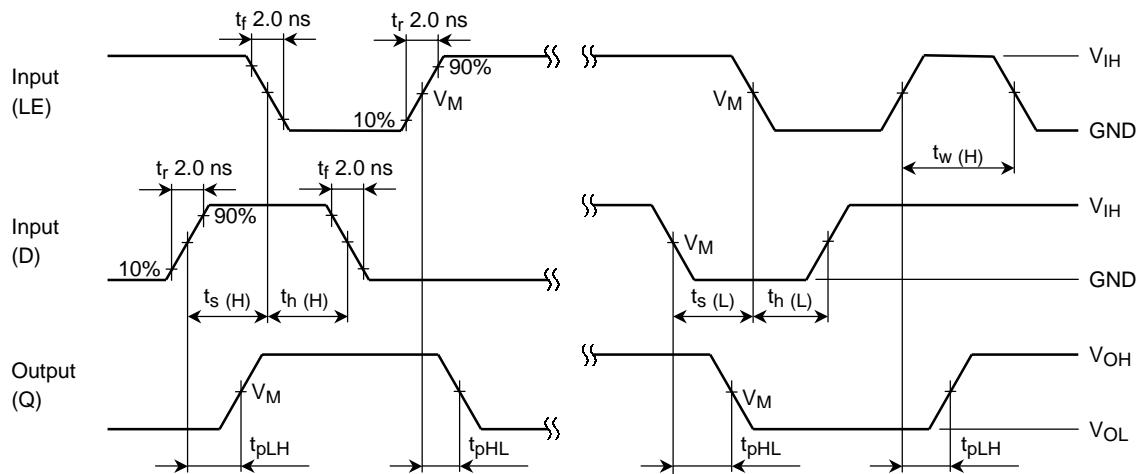
AC Test Circuit



Parameter	Switch
t_{PLH}, t_{PHL}	Open
t_{PLZ}, t_{PZL}	6.0 V @ $V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} \times 2$ @ $V_{CC} = 2.5 \pm 0.2 \text{ V}$ @ $V_{CC} = 1.8 \text{ V}$
t_{PHZ}, t_{PZH}	GND

Figure 1

AC Waveform

Figure 2 $t_{PLH}, t_{PHL}, t_w, t_s, t_h$

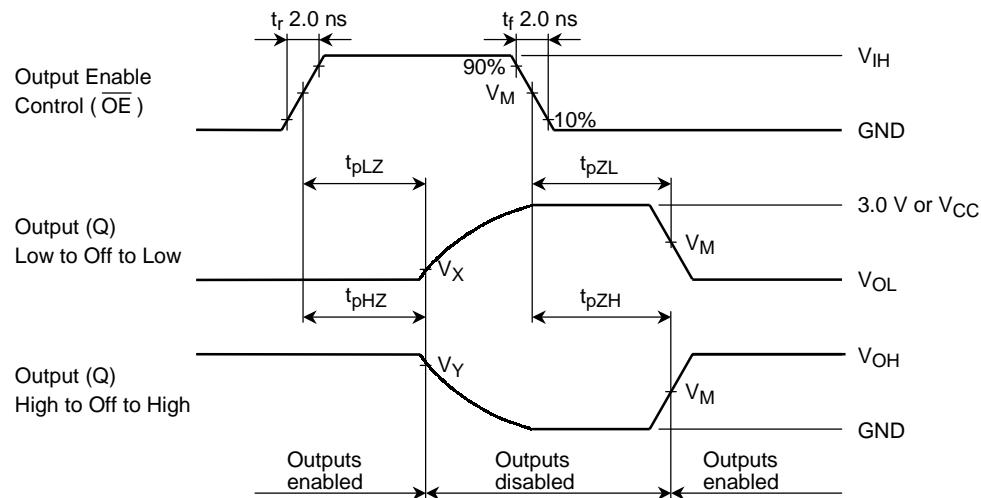


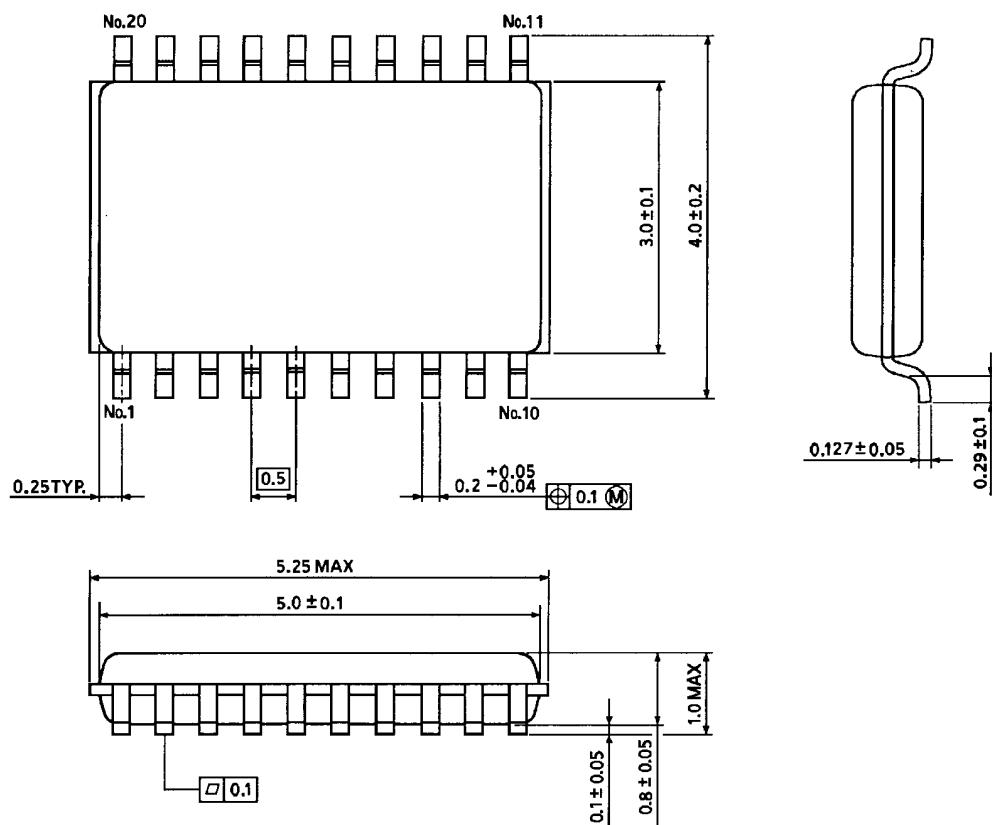
Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V_{CC}		
	$3.3 \pm 0.3 \text{ V}$	$2.5 \pm 0.2 \text{ V}$	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3 \text{ V}$	$V_{OL} + 0.15 \text{ V}$	$V_{OL} + 0.15 \text{ V}$
V_Y	$V_{OH} - 0.3 \text{ V}$	$V_{OH} - 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$

Package Dimensions

VSSOP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)

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